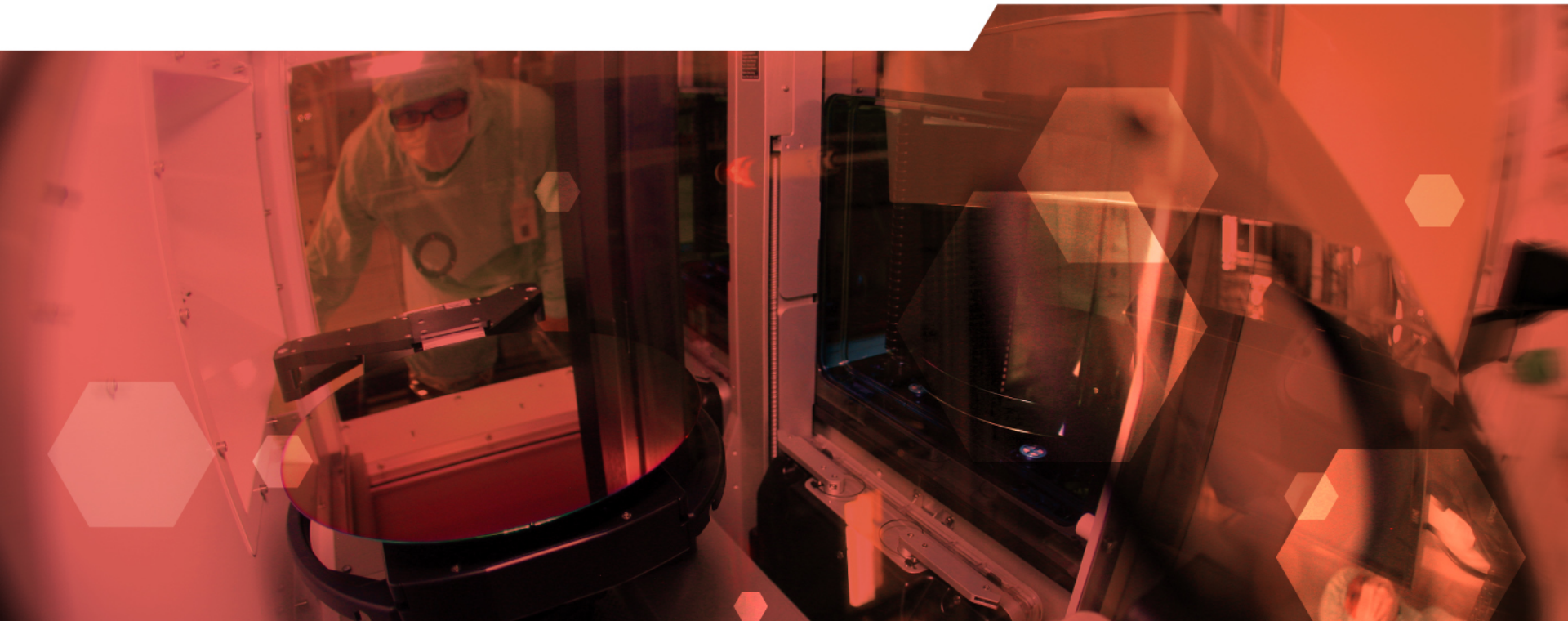


China HB-LED Committee Chapter Liaison Report

Sophia Huang

Updated May 22, 2017



Co-chairs



Dr. Yong Ji

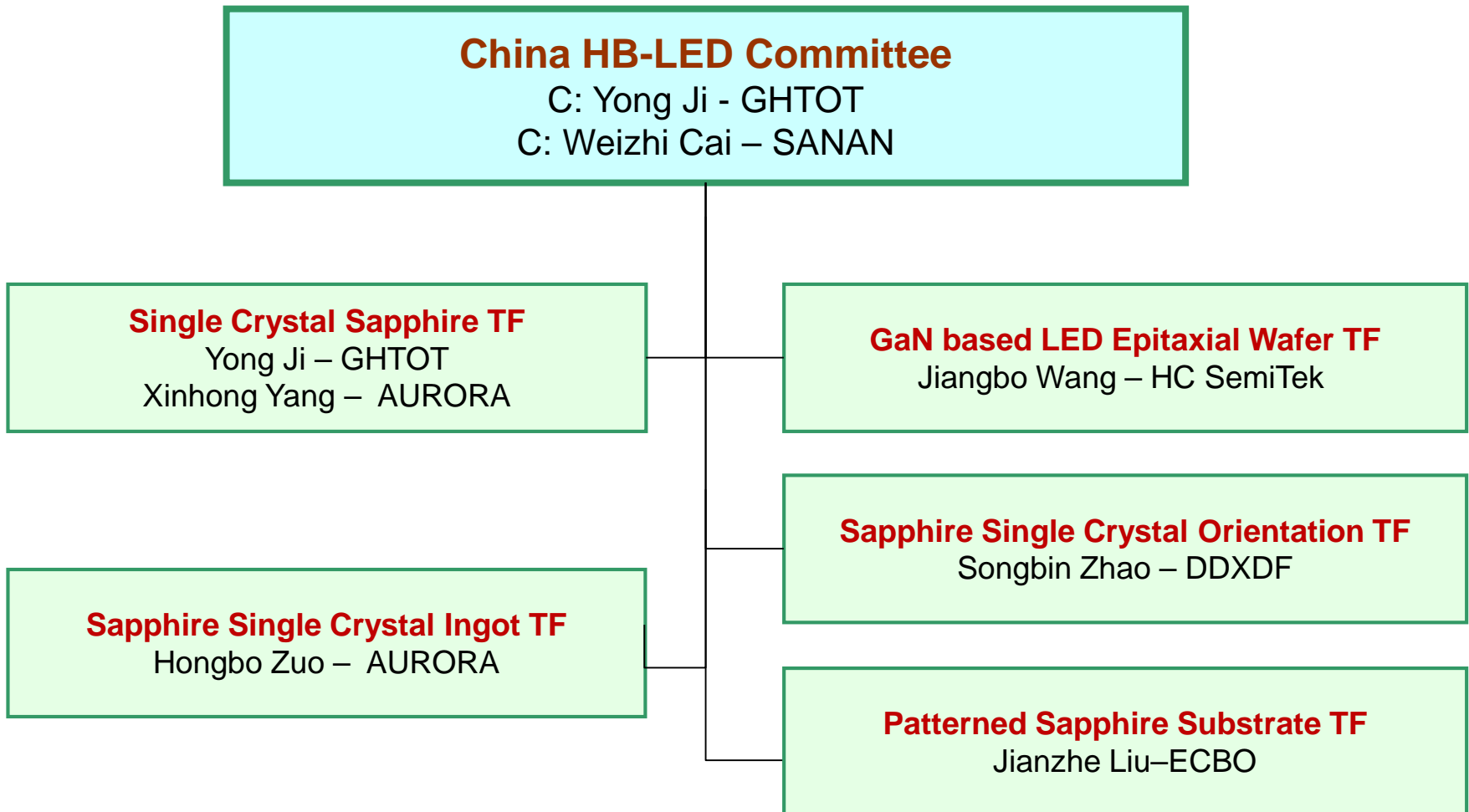
CEO of
Guizhou Haotian Optoelectronics
Technology Co., Ltd. China



Mr. Weizhi Cai

Vice CTO of
San'an Optoelectronics
Co., Ltd.

Organizational Chart



Meeting Information

- Last meeting

- China Standards Spring Meeting 2017
 - Wuhu, Anhui , China
 - Thursday, April 20, 2017

- Next meeting

- China Standards Fall Meeting 2017
 - Venue TBD
 - Wednesday, October 18, 2017

Single Crystal Sapphire Task Force

- Charter:
 - Draft the standards on specifications for single crystal sapphire intended for use for manufacturing HB-LED wafers.
- Working on:
 - Doc. 5723A, New Standard: Specification for Single Crystal Sapphire Intended for Use for Manufacturing HB- LED Wafers
 - Fail A&R Process, reballot in cycle 5-2017 or cycle 6-2017
 - Doc. 5946, New Standard: Test Method for Grain Boundary of Single Crystal Sapphire by Optical Homogeneity Technique (OHT)

Sapphire Single Crystal Ingot Task Force

- **Charter:**
 - Define the key parameters of LED sapphire ingot, including dimension, orientation of the end face and flat, surface quality, bulk defects, etc.
 - Formulate the inspection methods of the key parameters for LED sapphire ingot.
 - Formulate and establish inspection standards of the key parameters for LED sapphire ingot.
- **Working on:**
 - Doc. 5775A, New Standard: Specification for Sapphire Single Crystal Ingot Intended for Use for Manufacturing HB-LED Wafers
 - **Fail A&R Process, reballot in cycle 5-2017 or cycle 6-2017**

GaN based LED Epitaxial Wafer Task Force

- Charter:
 - This Task Force is chartered to develop test methods and specifications for GaN based HB-LED epitaxial wafer in order to increase the production efficiency.
- Working on:
 - Doc. 5776, New Standard: Test Method for Detecting Surface Defects of GaN based LED Epitaxial Wafer Used for Manufacturing HB-LED
 - Failed Cycle 8-2017 ballot, return to TF and reballot in Cycle 5-2017 or Cycle 6-2017

Sapphire Single Crystal Orientation Task Force

- **Charter:**
 - Develop the standards and measurement methods for the determination of orientations of sapphire single crystal products to enhance the consistency in measurement data and to provide the solutions for increasing measurement precision as well.
- **Working on:**
 - Doc. 5945, New Standard: Test Method for Determining Orientation of A Sapphire Single Crystal
 - Published as SEMI HB8-0217

Patterned Sapphire Substrate TF

- **Working on:**
 - New Standard: Specification for Dry Etching Patterned Sapphire Substrate (DPSS)
- **Plan for another SNARF on HB-LED China TC Chapter Fall meeting 2017:**
 - New Standard: Test Method Standard for The Uniformity of Patterns on Dry etching Patterned Sapphire Substrate (DPSS)

- **Four SNARFs Granted a One-Year Extension**

- Doc 5723B, Single Crystal Sapphire Task Force: New Standard: Specification for Single Crystal Sapphire Intended for Use for Manufacturing HB- LED Wafers
- Doc 5775B, Sapphire Single Crystal Ingot Task Force: New Standard: Specification for Sapphire Single Crystal Ingot Intended for Use for Manufacturing HB-LED Wafers
- Doc 5776A, GaN based LED Epitaxial Wafer Task Force: New Standard: Test Method for Detecting Surface Defects of GaN based LED Epitaxial Wafer Used for Manufacturing HB-LED
- Doc 5629, Single Crystal Sapphire Task Force: New Standard: Guide for Identification Defects on Bare Surfaces of Sapphire Wafers

Questions?

- **Contact**

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